DIGITRON SEMICONDUCTORS

Metal Oxide Field Effect Transistor (MOSFET) HR flow

All parts are screened per MIL-PRF-19500, JANTX Level and the device detail specification. All testing is performed at room temperature, unless indicated otherwise. For testing at high and low temperatures, Group A testing is required.

	Test	Method	Conditions / Notes
1	**Temperature Cycling**	*MIL-STD-750 Method 1051*	Test condition C or maximum storage temperature, whichever less. 20 cycles, 10 minutes per extreme.
2	**Interim Electrical Testing**		DC parameters per device detail specification.
3	**Gate Temperature Reverse Bias Burn-in**	*MIL-STD-750 Method 1042*	Condition B. 48 hours at 150°C and 80% of rated V_{GS}.
4	**Interim Electrical Testing**		DC parameters per device detail specification.
5	**High Temperature Reverse Bias Burn-in**	*MIL-STD-750 Method 1042*	Condition A. 160 hours at 150°C and 80% of rated V_{DS}.
6	**Final Electrical Testing**		DC parameters per device detail specification.
7	**Delta Calculation**		Delta parameters and limits per device detail specification.
8	**PDA Calculation**		10 percent defective allowed.
9	**Seal Test Fine Leak**	*MIL-STD-750 Method 1071*	Condition G or H
10	**Seal Test Gross Leak**	*MIL-STD-750 Method 1071*	Condition C

Notes:

1. Testing varies in accordance with the device detail specification.
2. Specific customer testing needs may be accommodated into any testing flow (selection tests, temperature requirements, special tests).

144 Market Street
Kenilworth NJ 07033 USA

phone +1.908.245-7200
fax +1.908.245-0555

sales@digitroncorp.com
www.digitroncorp.com